AT28C16

T-46-13-27

2

16K (2K x 8) CMOS E²PROM

Features

- Fast Read Access Time - 150ns
- Fast Byte Write - 200µs or 1 ms
- Self-Timed Byte Write Cycle
  - Internal Address and Data Latches
  - Internal Control Timer
  - Automatic Clear Before Write
- Direct Microprocessor Control
  - DATA POLLING
- Low Power
  - 30mA Active Current
  - 100µA CMOS Standby Current
- High Reliability
  - Endurance: 10^4 or 10^5 cycles
  - Data Retention: 10 years
- 5V ± 10% Supply
- CMOS & TTL Compatible Inputs and Outputs
- JEDEC Approved Byte Wide Pinout
- Full Military, Commercial, and Industrial Temperature Ranges

Description

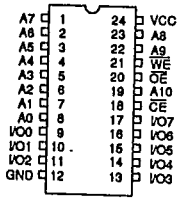
The AT28C16 is a low-power, high-performance Electrically Erasable and Programmable Read Only Memory with easy to use features. The AT28C16 is a 16k memory organized as 2,048 words x 8 bits. The device is manufactured with Atmel's reliable non-volatile CMOS technology.

The AT28C16 is accessed like a static RAM for the read or write cycles without the need of external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The end of a write cycle can be determined by DATA polling of I/O7. Once the end of a write cycle has been detected, a new access for a read or a write can begin.

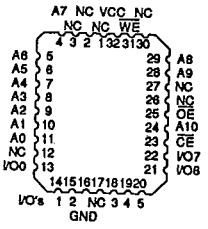
The CMOS technology offers fast access times of 150ns at low power dissipation. When the chip is deselected the standby current is less than 100µA.

Atmel's 28C16 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of E^2PROM are available for device identification or tracking.

Pin Configurations

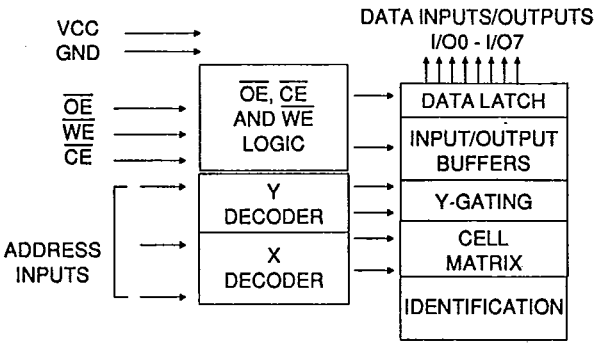


Pin Name	Function
A0 - A10	Addresses
$\overline{CE}$	Chip Enable
$\overline{OE}$	Output Enable
$\overline{WE}$	Write Enable
I/O0 - I/O7	Data Inputs/Outputs
NC	No Connect



Note: PLCC package pins 1 and 17 are DON'T CONNECT.

Block Diagram



Operating Modes

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O
Read	V_{IL}	V_{IL}	V_{IH}	D_{OUT}
Write[2]	V_{IL}	V_{IH}	V_{IL}	D_{IN}
Standby/Write Inhibit	V_{IH}	X[1]	X	High Z
Write Inhibit	X	X	V_{IH}	
Write Inhibit	X	V_{IL}	X	
Output Disable	X	V_{IH}	X	High Z
Chip Erase	V_{IL}	V_H [3]	V_{IL}	High Z

Notes: 1. X can be V_{IL} or V_{IH}.
2. Refer to A.C. Programming Waveforms.
3. $V_H = 12.0V \pm 0.5V$.

Device Operation

READ: The AT28C16 is accessed like a Static RAM. When $\overline{CE}$ and $\overline{OE}$ are low and $\overline{WE}$ is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever $\overline{CE}$ or $\overline{OE}$ is high. This dual line control gives designers increased flexibility in preventing bus contention.

BYTE WRITE: Writing data into the AT28C16 is similar to writing into a Static RAM. A low pulse on the $\overline{WE}$ or $\overline{CE}$ input with $\overline{OE}$ high and $\overline{CE}$ or $\overline{WE}$ low (respectively) initiates a byte write. The address location is latched on the last falling edge of $\overline{WE}$ (or $\overline{CE}$); the new data is latched on the first rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion.

FAST BYTE WRITE: The AT28C16F offers a byte write time of 200µs maximum. This feature allows the entire device to be rewritten in 0.4 seconds.

$\overline{DATA}$ POLLING: The AT28C16 provides $\overline{DATA}$ POLLING to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in the complement of that data for I/O_7 (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

WRITE PROTECTION: Inadvertent writes to the device are protected against in the following ways. (a) Vcc sense— if Vcc is below 3.8V (typical) the write function is inhibited. (b) Vcc power on delay— once Vcc has reached 3.8V the device will automatically time out 5ms (typical) before allowing a byte write. (c) Write Inhibit— holding any one of $\overline{OE}$ low, $\overline{CE}$ high or $\overline{WE}$ high inhibits byte write cycles.

CHIP CLEAR: The contents of the entire memory of the AT28C16 may be set to the high state by the CHIP CLEAR operation. By setting $\overline{CE}$ low and $\overline{OE}$ to 12 volts, the chip is cleared when a 10 msec low pulse is applied to $\overline{WE}$.

DEVICE IDENTIFICATION: An extra 32 bytes of E^2PROM memory are available to the user for device identification. By raising A9 to 12 ± 0.5V and using address locations 7E0H to 7FFH the additional bytes may be written to or read from in the same manner as the regular memory array.

Absolute Maximum Ratings*

Temperature Under Bias	-55°C to +125°C
Storage Temperature	-65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground	-0.6V to +6.25V
All Output Voltages with Respect to Ground	-0.6V to Vcc +0.6V
Voltage on $\overline{OE}$ and A9 with Respect to Ground	-0.6V to +13.5V

*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

D.C. and A.C. Operating Range

		AT28C16-15	AT28C16-20	AT28C16-25
Operating Temperature (Case)	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C
	Ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
Vcc Power Supply		5V±10%	5V±10%	5V±10%

D.C. Characteristics

Symbol	Parameter	Condition		Min	Max	Units
I_{LI}	Input Load Current	V_{IN}=0V to Vcc + 1V			10	µA
I_{LO}	Output Leakage Current	$V_{I/O}$=0V to Vcc			10	µA
I_{SB1}	Vcc Standby Current CMOS	$\overline{CE}$=Vcc-0.3V to Vcc + 1.0V			100	µA
I_{SB2}	Vcc Standby Current TTL	$\overline{CE}$=2.0V to Vcc + 1.0V	Com.		2	mA
			Ind., Mil.		3	mA
I_{CC}	Vcc Active Current A.C.	f=5MHz; I_{OUT}=0mA $\overline{CE}$=V_{IL}	Com.		30	mA
			Ind., Mil.		45	mA
V_{IL}	Input Low Voltage				0.8	V
V_{IH}	Input High Voltage			2.0		V
V_{OL}	Output Low Voltage	I_{OL}=2.1mA			.4	V
V_{OH}	Output High Voltage	I_{OH}=-400µA		2.4		V

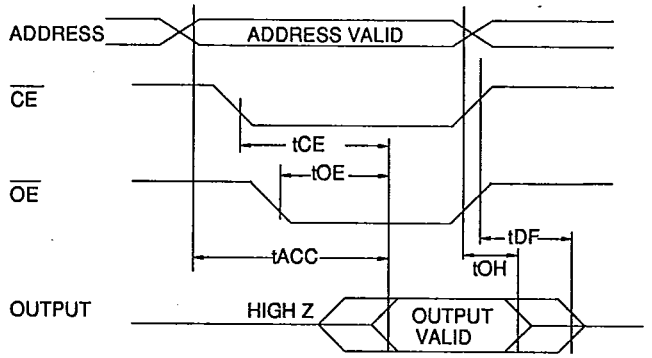
Pin Capacitance (f=1MHz T=25°C) [4]

	Typ	Max	Units	Conditions
C_{IN}	4	6	pF	V_{IN} = 0V
C_{OUT}	8	12	pF	V_{OUT} = 0V

A.C. Read Characteristics

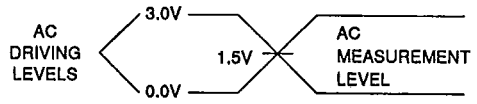
Symbol	Parameter	AT28C16-15		AT28C16-20		AT28C16-25		Units
		Min	Max	Min	Max	Min	Max	
t_{ACC}	Address to Output Delay		150		200		250	ns
t_{CE} (1)	$\overline{CE}$ to Output Delay		150		200		250	ns
t_{OE} (2)	$\overline{OE}$ to Output Delay	10	70	10	80	10	100	ns
t_{DF} (3,4)	$\overline{CE}$ or $\overline{OE}$ High to Output Float	0	50	0	55	0	60	ns
t_{OH}	Output Hold from $\overline{OE}$, $\overline{CE}$ or Address, whichever occurred first	0		0		0		ns

A.C. Read Waveforms



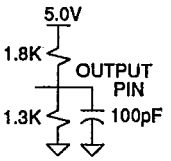
Notes:
1. $\overline{CE}$ may be delayed up to $t_{ACC} - t_{CE}$ after the address transition without impact on t_{ACC}.
2. $\overline{OE}$ may be delayed up to $t_{CE} - t_{OE}$ after the falling edge of $\overline{CE}$ without impact on t_{CE} or by $t_{ACC} - t_{OE}$ after an address change without impact on t_{ACC}.
3. t_{DF} is specified from $\overline{OE}$ or $\overline{CE}$ whichever occurs first (C_L = 5pF).
4. This parameter is characterized and is not 100% tested.

Input Test Waveforms and Measurement Level



t_R, t_F < 20ns

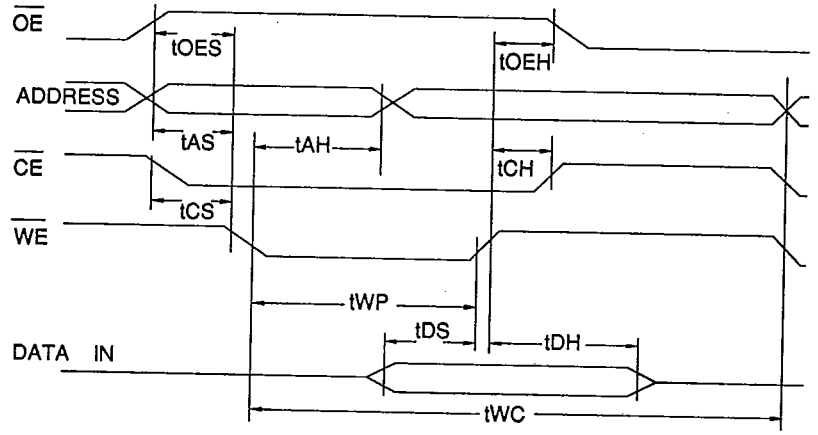
Output Test Load



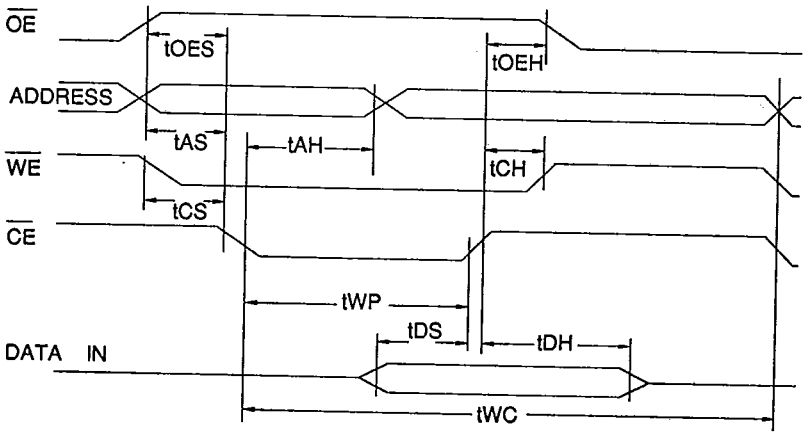
A.C. Write Characteristics

Symbol	Parameter		Min	Typ	Max	Units
t_{AS}, t_{OES}	Address, $\overline{OE}$ Set-up Time		10			ns
t_{AH}	Address Hold Time		50			ns
t_{WP}	Write Pulse Width ($\overline{WE}$ or $\overline{CE}$)		100		1000	ns
t_{DS}	Data Set-up Time		50			ns
t_{DH},t_{OEH}	Data, $\overline{OE}$ Hold Time		10			ns
t_{WC}	Write Cycle Time	AT28C16		0.5	1.0	ms
		AT28C16E/F		100	200	µs

A.C. Write Waveforms- $\overline{WE}$ Controlled



A.C. Write Waveforms- $\overline{CE}$ Controlled

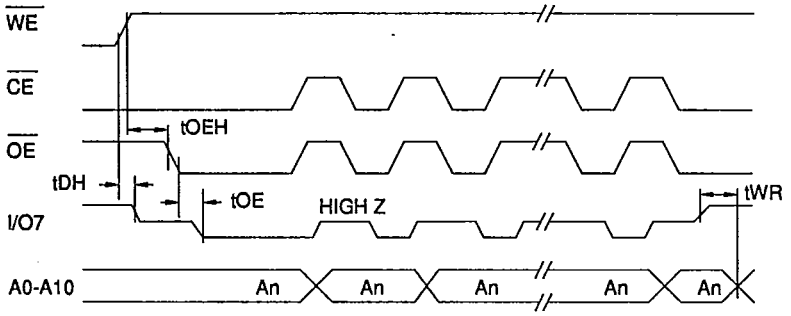


$\overline{\text{Data}}$ Polling Characteristics[1]

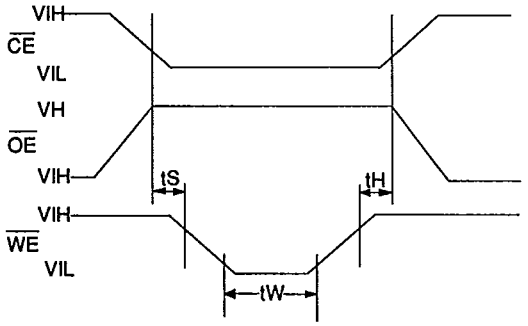
Symbol	Parameter	Min	Typ	Max	Units
t_{DH}	Data Hold Time	10			ns
t_{OEH}	$\overline{OE}$ Hold Time	10			ns
t_{OE}	$\overline{OE}$ to Output Delay			100	ns
t_{WR}	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

$\overline{\text{Data}}$ Polling Waveforms

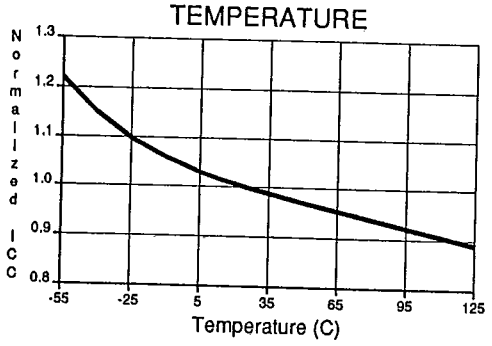


Chip Erase Waveforms

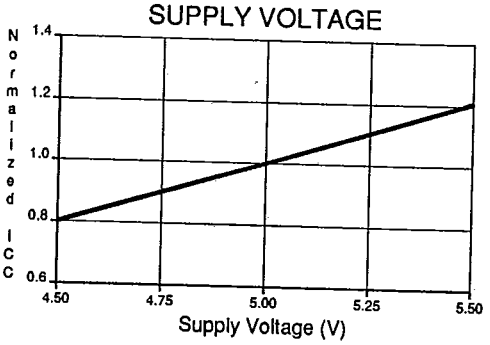


$t_S = t_H = 1\mu sec$ (min.)
$t_W = 10msec$ (min.)
$V_H = 12.0V \pm 0.5V$

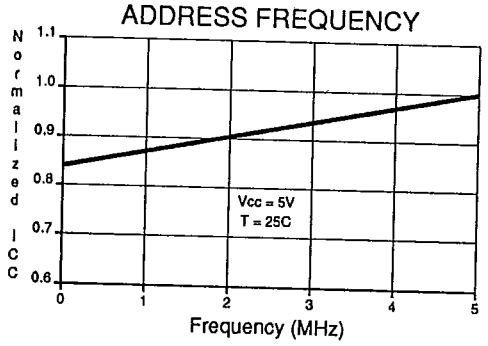
NORMALIZED SUPPLY CURRENT vs. TEMPERATURE



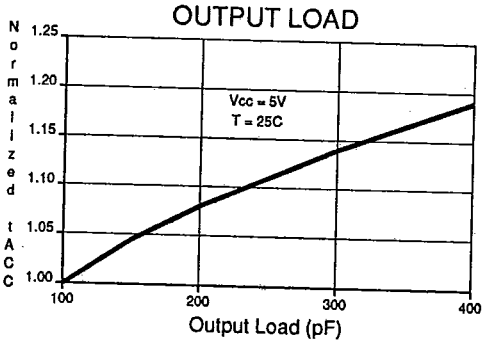
NORMALIZED SUPPLY CURRENT vs. SUPPLY VOLTAGE



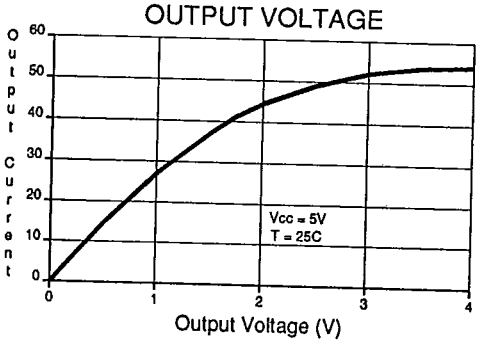
NORMALIZED SUPPLY CURRENT vs. ADDRESS FREQUENCY



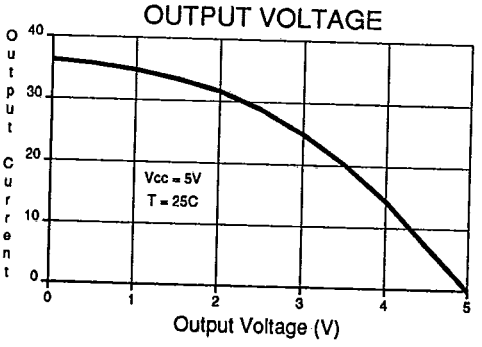
NORMALIZED ACCESS TIME vs. OUTPUT LOAD



OUTPUT SINK CURRENT vs. OUTPUT VOLTAGE



OUTPUT SOURCE CURRENT vs. OUTPUT VOLTAGE



Ordering Information

tACC (ns)	Icc (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
150	30	0.1	AT28C16(E,F)-15DC AT28C16(E,F)-15JC AT28C16(E,F)-15LC AT28C16(E,F)-15PC AT28C16(E,F)-15SC	24D6 32J 32L 24P6 24S	Commercial (0°C to 70°C)
150	45	0.1	AT28C16(E,F)-15DI AT28C16(E,F)-15JI AT28C16(E,F)-15LI AT28C16(E,F)-15PI AT28C16(E,F)-15SI	24D6 32J 32L 24P6 24S	Industrial (-40°C to 85°C)
			AT28C16(E,F)-15DM AT28C16(E,F)-15LM	24D6 32L	Military (-55°C to 125°C)
			AT28C16(E,F)-15DM/883 AT28C16(E,F)-15LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	30	0.1	AT28C16(E,F)-20DC AT28C16(E,F)-20JC AT28C16(E,F)-20LC AT28C16(E,F)-20PC AT28C16(E,F)-20SC	24D6 32J 32L 24P6 24S	Commercial (0°C to 70°C)
200	45	0.1	AT28C16(E,F)-20DI AT28C16(E,F)-20JI AT28C16(E,F)-20LI AT28C16(E,F)-20PI AT28C16(E,F)-20SI	24D6 32J 32L 24P6 24S	Industrial (-40°C to 85°C)
			AT28C16(E,F)-20DM AT28C16(E,F)-20LM	24D6 32L	Military (-55°C to 125°C)
			AT28C16(E,F)-20DM/883 AT28C16(E,F)-20LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	30	0.1	AT28C16(E,F)-25DC AT28C16(E,F)-25JC AT28C16(E,F)-25LC AT28C16(E,F)-25PC AT28C16(E,F)-25SC AT28C16-W	24D6 32J 32L 24P6 24S DIE	Commercial (0°C to 70°C)
250	45	0.1	AT28C16(E,F)-25DI AT28C16(E,F)-25JI AT28C16(E,F)-25LI AT28C16(E,F)-25PI AT28C16(E,F)-25SI	24D6 32J 32L 24P6 24S	Industrial (-40°C to 85°C)
			AT28C16(E,F)-25DM AT28C16(E,F)-25LM	24D6 32L	Military (-55°C to 125°C)
			AT28C16(E,F)-25DM/883 AT28C16(E,F)-25LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Ordering Information

T-46-13-27

tACC (ns)	Icc (mA)		Ordering Code	Package	Operation Range
	Active	Standby			
300	45	0.1	AT28C16(E,F)-30DM/883 AT28C16(E,F)-30LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	45	0.1	AT28C16(E,F)-35DM/883 AT28C16(E,F)-35LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
450	45	0.1	AT28C16(E,F)-45DM/883 AT28C16(E,F)-45LM/883	24D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type	
24D6	24 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)
24P6	24 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)
24S	24 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)
W	Die
Options	
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms
E	High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 µs
F	Fast Write Option: Write Time = 200 µs